

# Stereo Crystal Ecal: Input Materials

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For Stereo Crystal Ecal study team

Updated:

1: refined electronics design

3: refined mechanics design

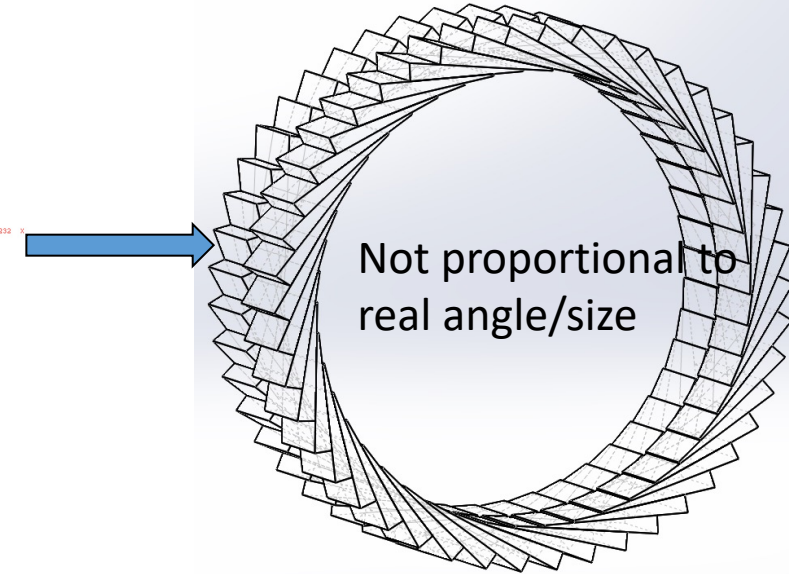
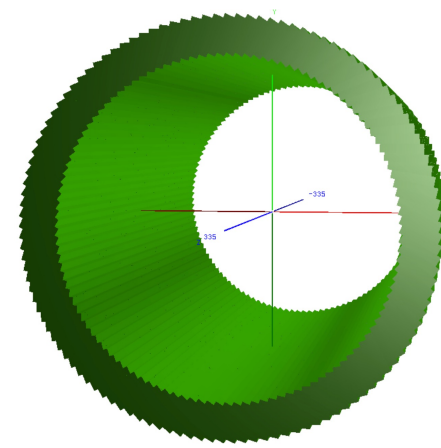
5: comparison of SiPM/APD/PD

2: refined endcap conceptual design

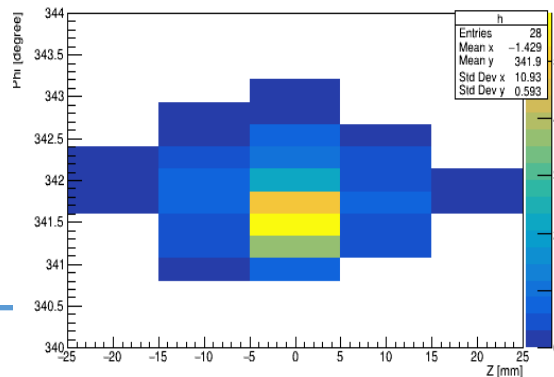
4: gamma + charged pi separation

# Stereo Crystal Electromagnetic Calorimeter: Design

- To improve the 3D position resolution
  - Pointing angle of **even layers** along Z:  $\alpha$
  - Pointing angle of odd layers along Z:  $\alpha' = -\alpha$
- Benchmark design:
  - $\alpha = 20$  degrees
  - R segmentation = 10
  - Crystal:  $(8-8.1) \times 10 \times 284 \text{ mm}^3$
  - Readout: **SiPM (or APD/PD) + electronics**
  - Cooling pipe planted into the outside of the mechanical support
  - **24X0+10mm electronics+10mm support + 10 mm contingency = 300mm**

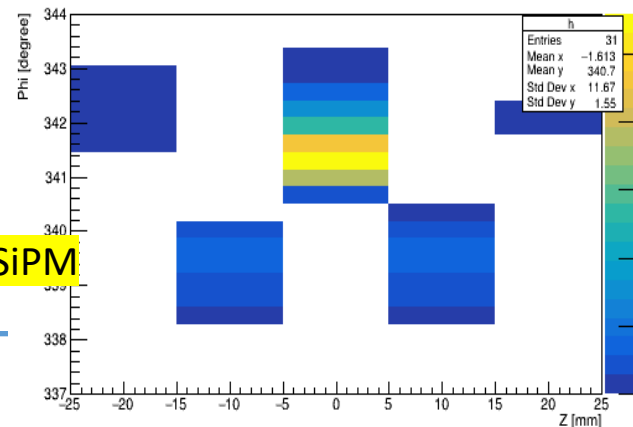


Traditional Crystal Ecal



**BGO+SiPM**

SCEcal



Left eye

Right eye

# Performance

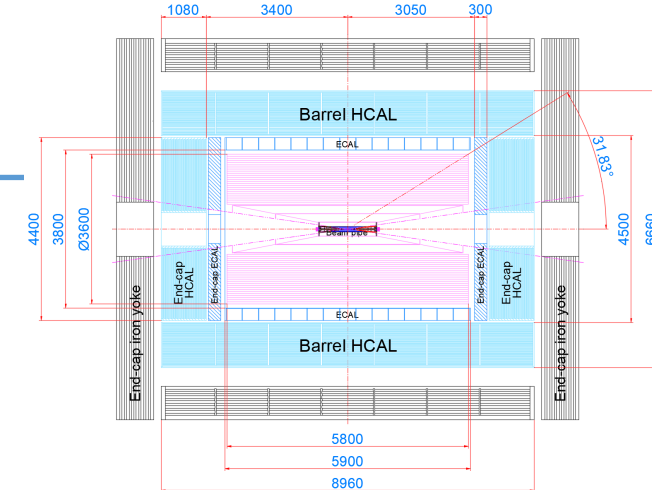
Items	Priority	Results / Status	Remarks
Boson Mass Resolution	A	H→di-photon: 0.3%(1.3%) with 2MeV(50MeV) thr. H→gg is under study	BMR < 4% CEPCSW fullsim
Intrinsic EM/hadronic energy resolution	A	Stochastic term: 0.9%(3.2%)/sqrt(E) with 2MeV(50MeV) thr.	CEPCSW fullsim
Separation power		5 GeV gamma/gamma, >80%@15mm 5 GeV gamma/10 GeV Pi: >60%@15mm	CEPCSW fullsim
Lepton ID in jets		preparing	Clear shape difference seen(backup)
Timing capability		Could have, accuracy depending on the sensitive material	No showstopper
$\pi^0$ reconstruction		Studying	CEPCSW fullsim
Pile-up at Z-pole		-	No showstopper

- Priority/importance for performance requirements: (A) must-have; (B) plus; (C) not essential

# Cost

Cost table template for ECAL

Parameter Name	Barrel	Endcaps (x2)	Sum
Inner Radius for ECAL	1900 mm	350 mm	NA
Length for barrel; Outer radius for endcap	5900 mm	1900 mm + $24X_0$	NA
Longitudinal Depth	$24X_0$ (Thickness depends on each option)		NA
Modularity	#modules in phi, #rings along Z	Assuming ideal geometry if no design?	NA
Material Volume (m <sup>3</sup> )	20.26	7.27	27.5
Readout channels	827180	320040	1,144,428
Power dissipation (kW)	16.5kW	6.4kW	<b>22.9kW</b>
Cost: sensitive materials	1316.9M RMB	472.5M RMB	<b>1789M RMB</b>
Cost: electronics	62.8M RMB	24.3M RMB	<b>87M RMB</b>
			<b>1876 MRMB</b>



## SiPM + Electronics

- SiPM: 56RMB/piece
- Electronics: 20RMB/ch

## BGO:

- BGO: **65RMB/cc (SIC)**
  - (R.Y. Zhu 42-50RMB/cc)

## Power:

- 20mW/ch (Half of HGCal/ch)

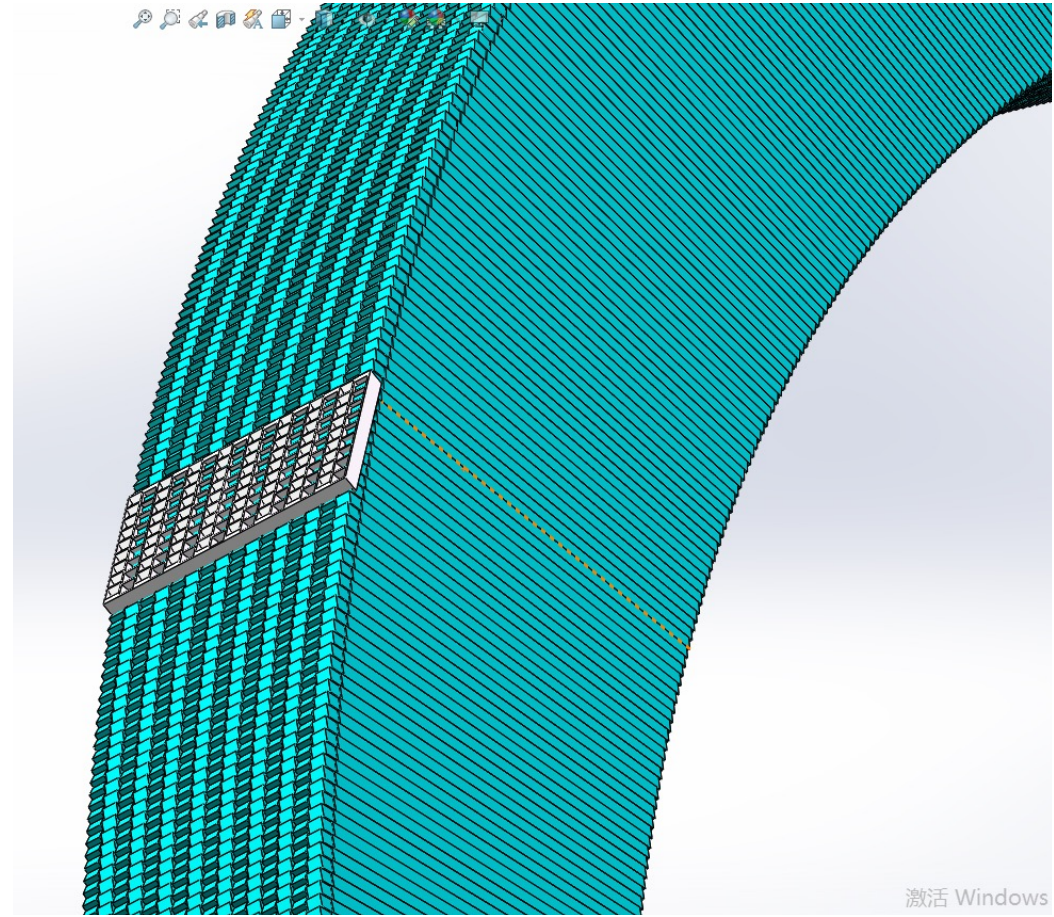
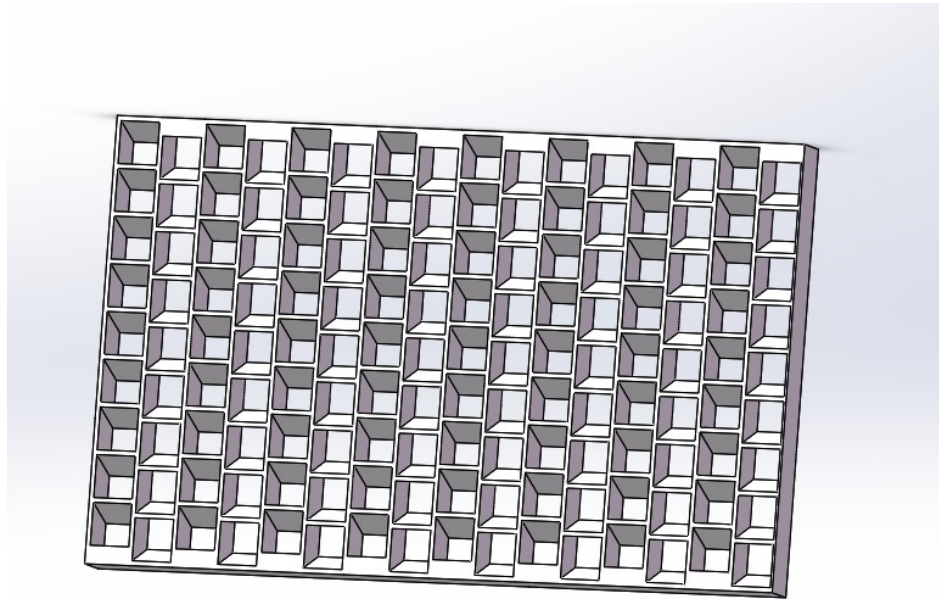
# Technical readiness level

- Status and plans of simulation studies and R&D (a table template)
- Person power: Xiao ZHAO, Chaochen Yuan, Han WANG, Liheng Huang, Lianyou Shan, Huaqiao ZHANG, Yunlong ZHANG

Category	Status	Design 1	Other Alternative Design (if any)
Technical Readiness Level	Full Simulation (system level)	V1 Implemented in CEPCSW	
	Full Simulation (module level)	V1 Implemented in CEPCSW	
	Prototyping R&D (common)	L3 Ecal, CEPC 4D crystal Ecal	
	Prototyping R&D (modules, units)		No BGO module, GEO with Sc. In preparing



1	桶部	单位 (毫米)					
2	内部直径	3800	最大外部直径	4400	长度	5900	
3	晶体	BGO (24X0=26.88cm)	市场参考价格: ¥ 65.00/cc				
4	大小	(8.0-8.1)*10*284	数量	827180=1402*590	体积	20.26m3	
5	重量	144.5吨	价格	13.169亿			
6	机械设计	纯圆桶					
7	外径面支撑/悬挂		内径面辅助		轴向20个单元		
8	竖直组装, 旋转90度后推入						
9	总厚度:	24X0 + 1cm电子学 + 1-2cm支撑=300mm					
10							
11	端盖*2	单位 (毫米)					
12	内部直径	700	外部直径	3800+2*24X0	厚度	24X0*2	
13	晶体	BGO (24X0)	市场参考价格: ¥ 65/cc				
14	大小	8*10*284	数量	317248	体积	7.27 m3	
15	重量	51.8吨	价格	4.725亿			
16	机械设计						
17	内径面支撑, 外表面固定						
18	总厚度:	24X0 + 1cm电子学 + 1-2cm支撑=300mm					
19							
20	电子学	1,147,220=827180+320040					
21	前端板	1.6mm	母版	1.6mm	间隙	2mm	
22	功耗	22.9kW(20mw/channel)	电子学价格	20/ch			
23	SiPM	56/ch	总价格	87MRMB			
24	散热系统	厚度2mm					



激活 Windows

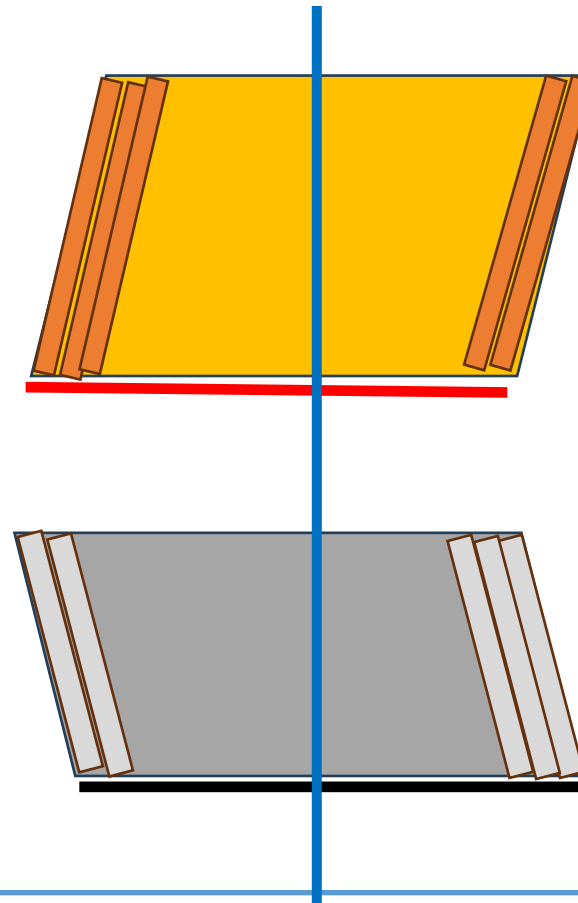
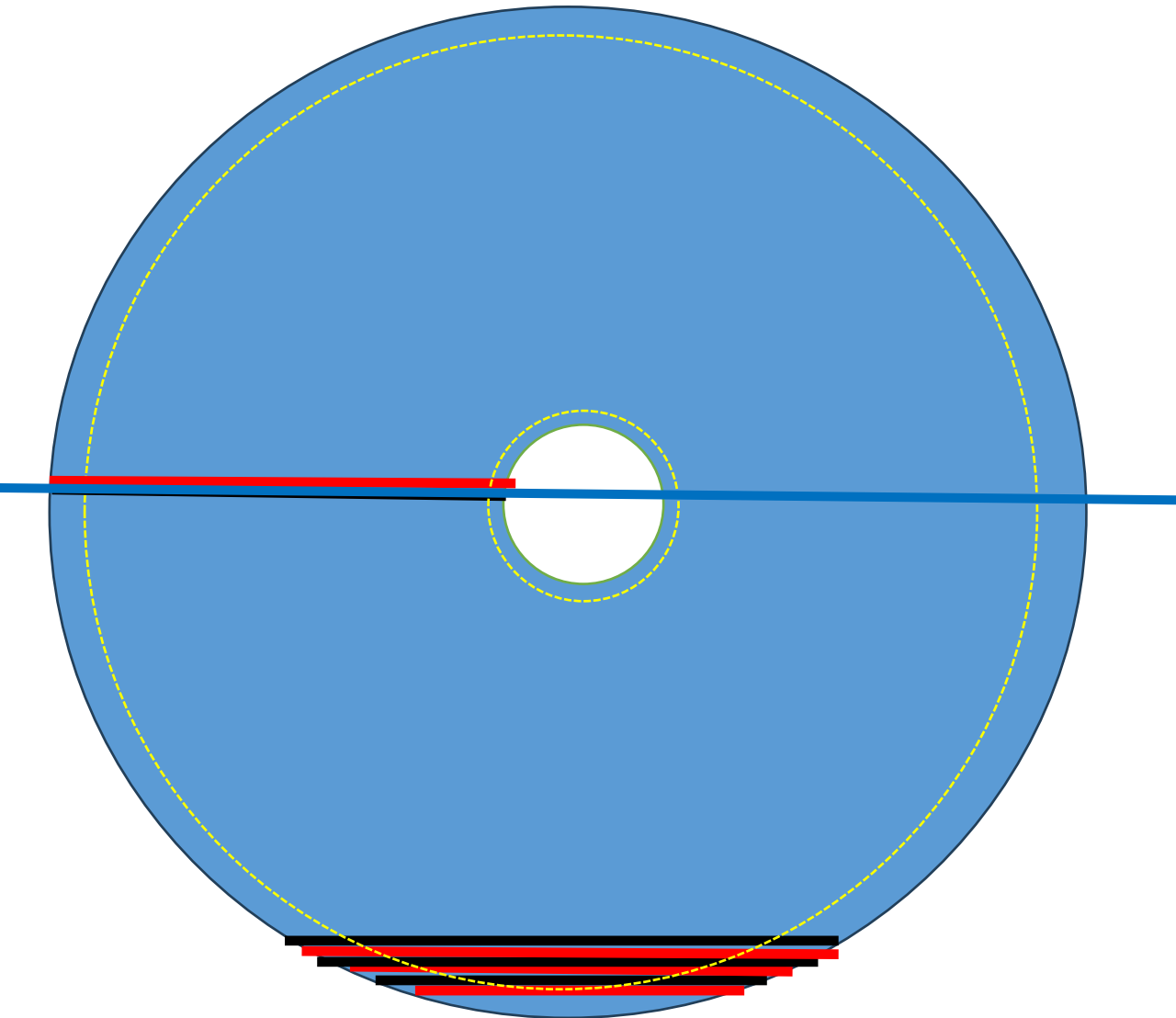


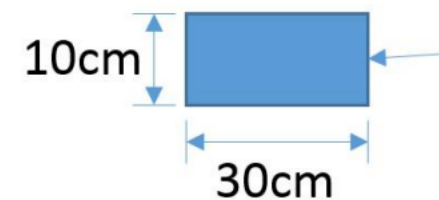
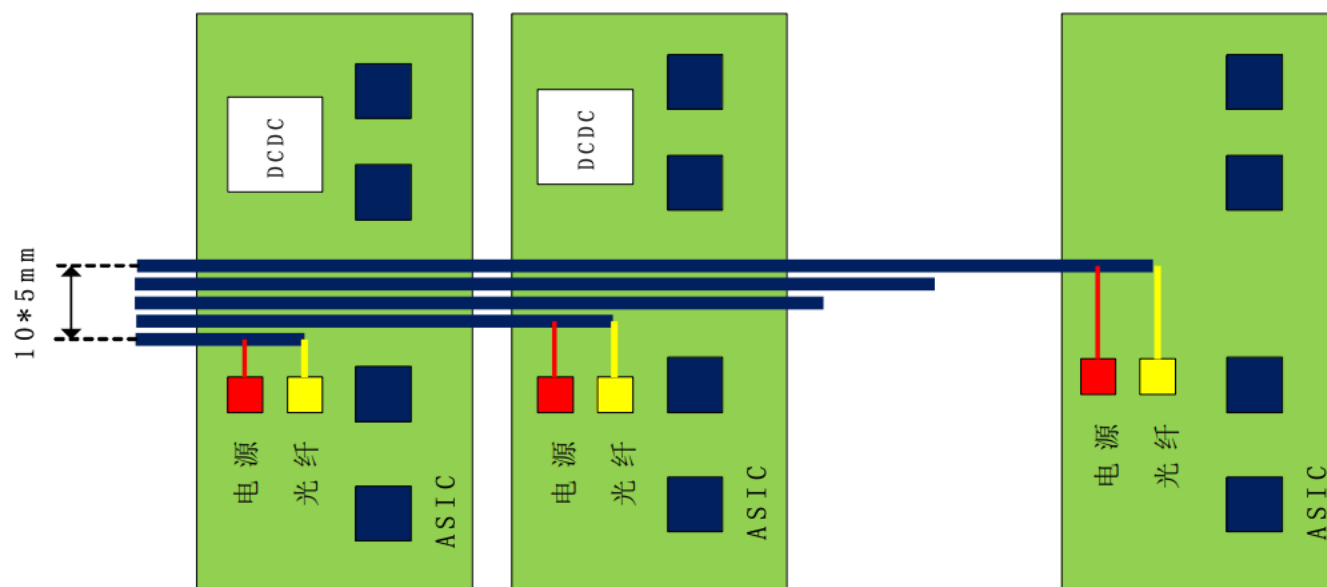
# Endcap conceptual design: 机械设计→少静

Crystal: 8\*10\*284mm

Horizontal layers has same point angle

Pointing angle defined as angle w.r.t. beam in the horizontal plane: 20 degree



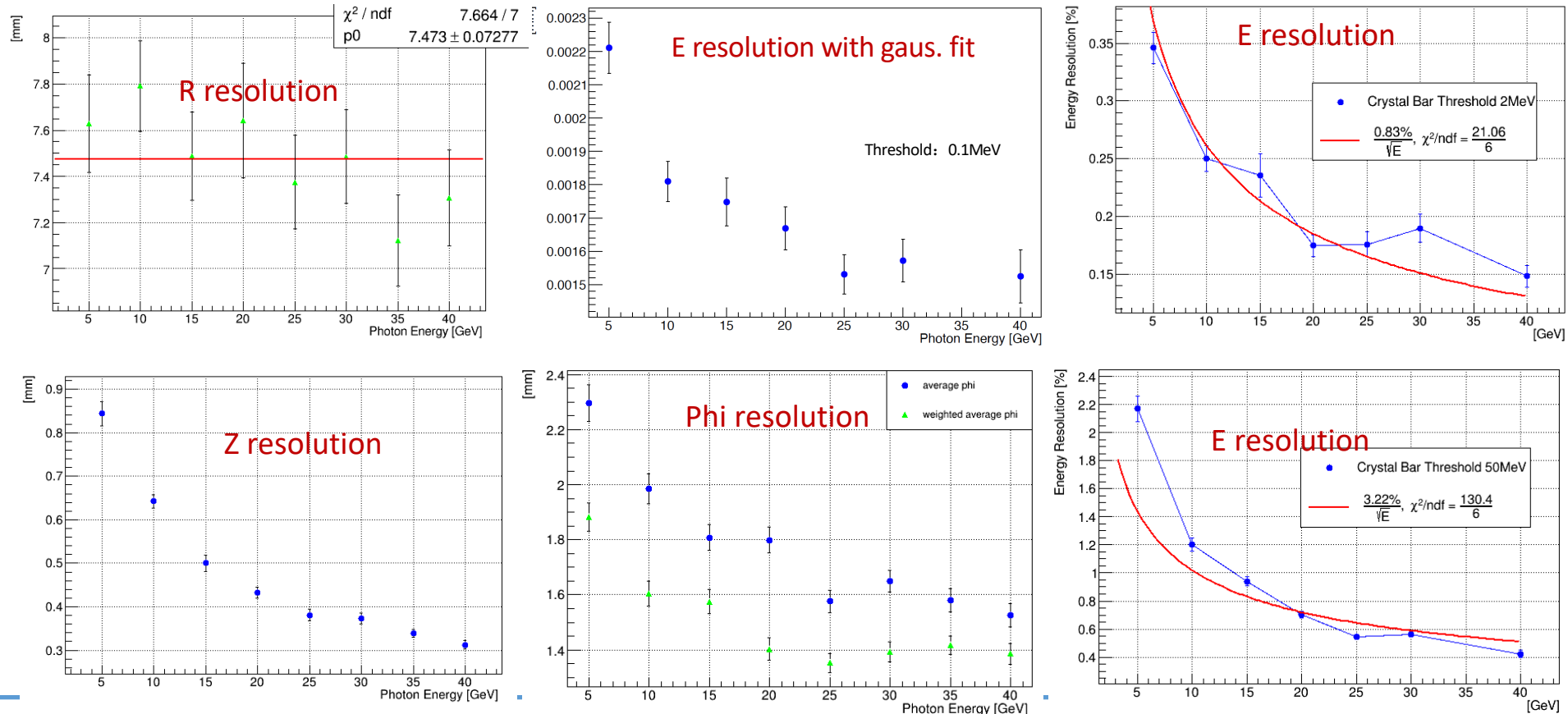


$12 * 30 = 360$ 个晶体

晶体尺寸:  
 $10 * 8 * 284\text{mm}$

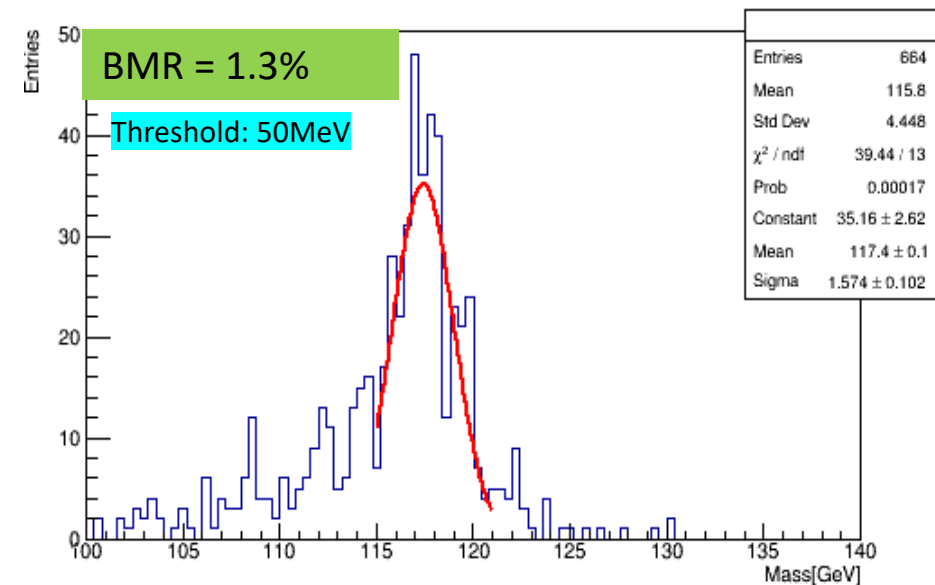
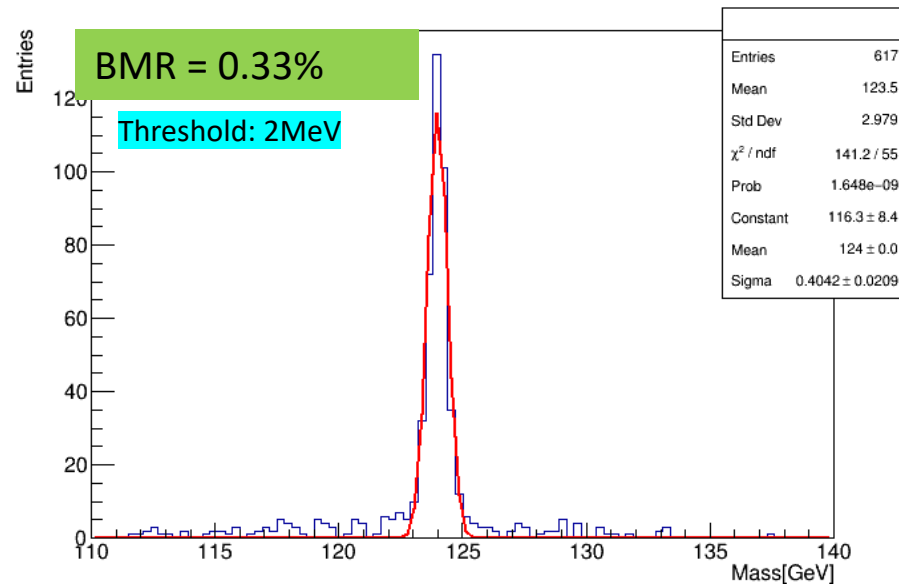
# Performance of Energy and 3D positioning resolution

- 5GeV gamma, phi: 10~350°, theta: 90°
  - ◆ Z resolution ~ 0.84 mm;      Phi resolution ~ 1.9 mm
  - ◆ R resolution ~ 7.6 mm;      Energy resolution as function of energy



# Boson mass resolution in $H \rightarrow \gamma\gamma$

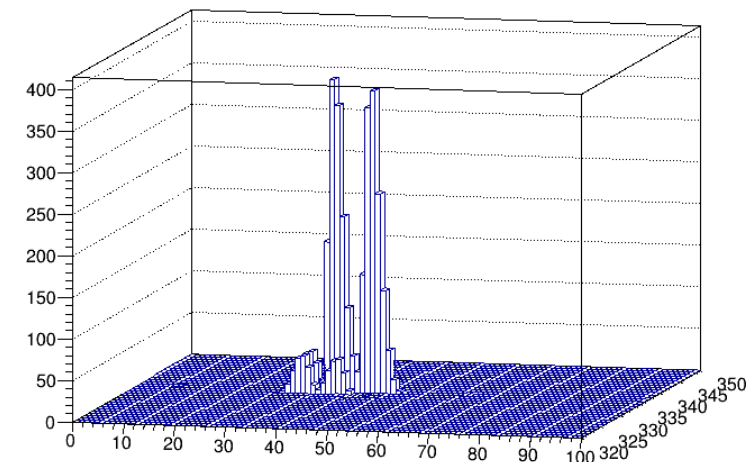
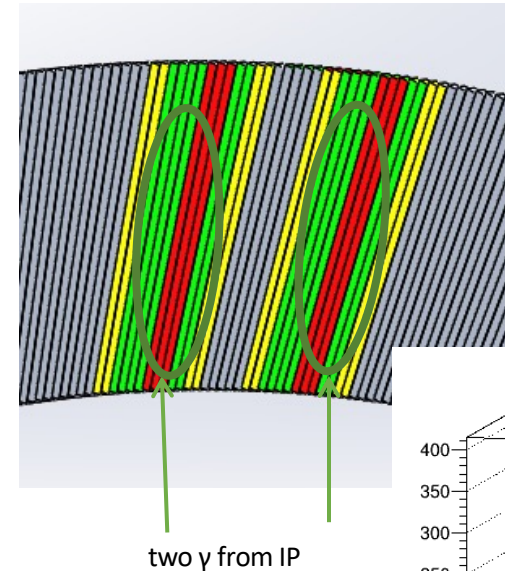
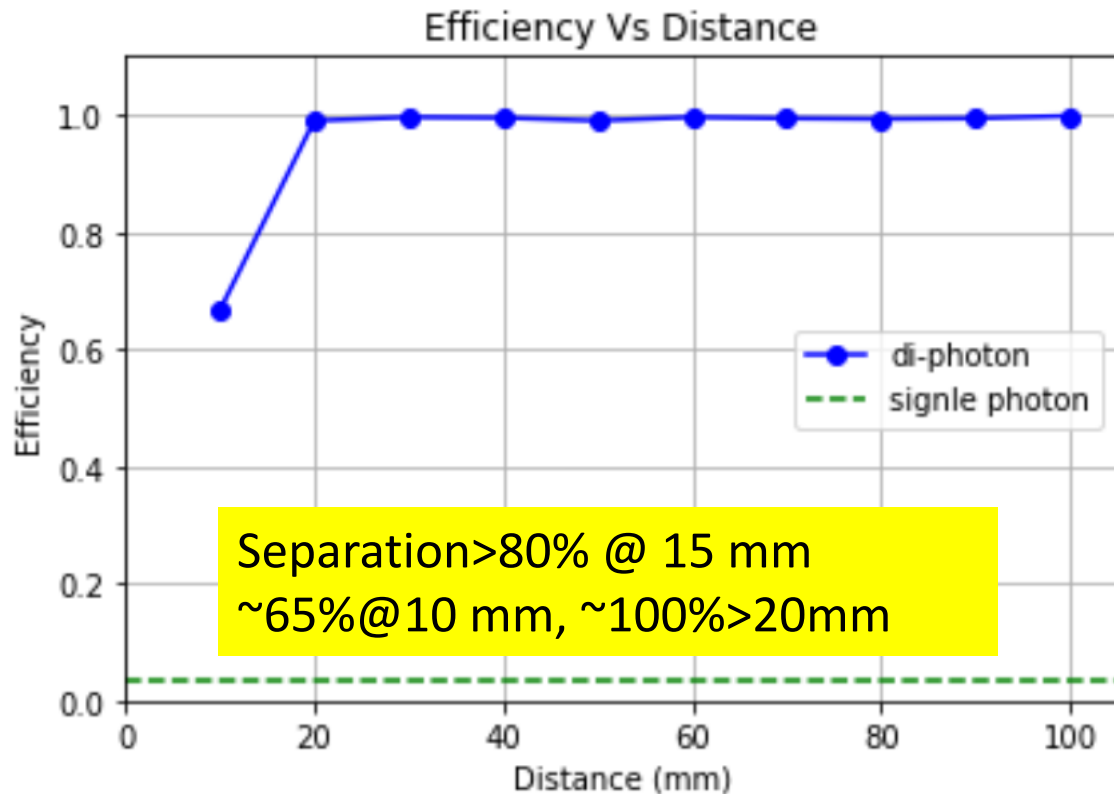
- Sample:  $ZH \rightarrow 2\text{neutrinos} + \gamma\gamma$  at 240 GeV
- Energy, position reconstruction and separation using simplified reconstruction method described above
- Crystal energy threshold: 2 MeV/50MeV



# Separation between two 5 GeV photons

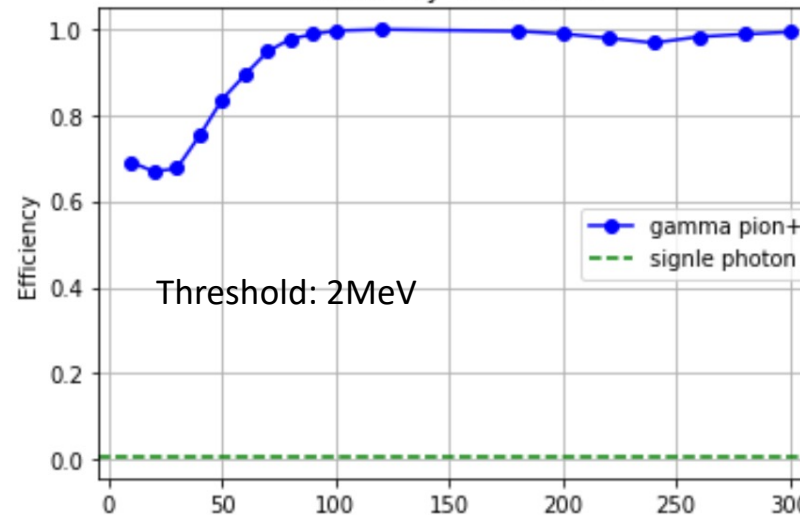
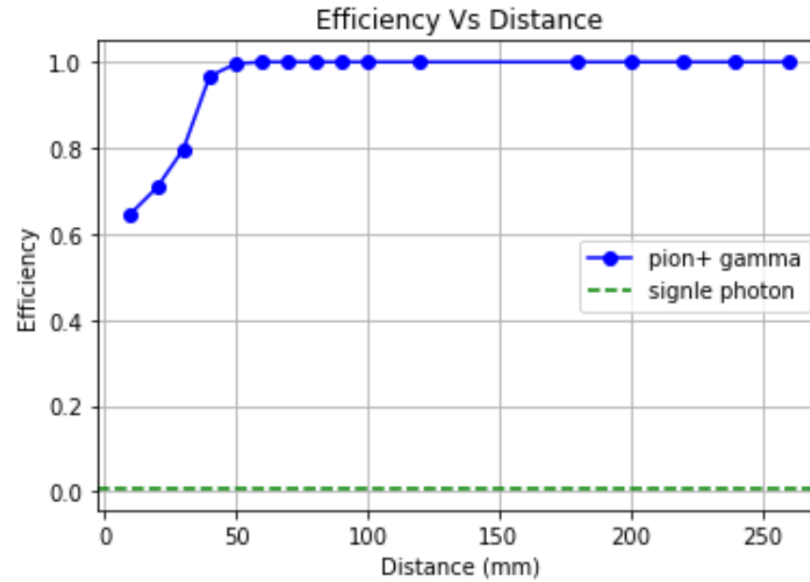
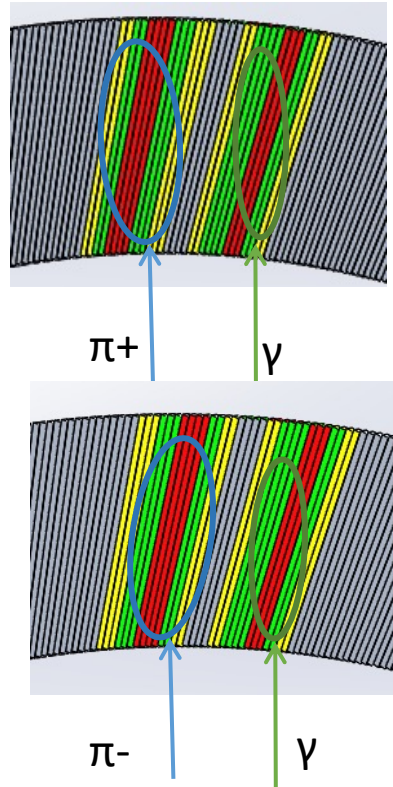
- Two 5 GeV photons, vary distance along phi between them
- Success reconstruction: 2 neutral particles,  $3.3\text{GeV} < E_\gamma < 6.6\text{GeV}$  for each photon
- Separation and energy regression using end-to-end NN
  - trained with flat distributed photon energy and distances

<https://journals.aps.org/prd/pdf/10.1103/PhysRevD.108.052002>

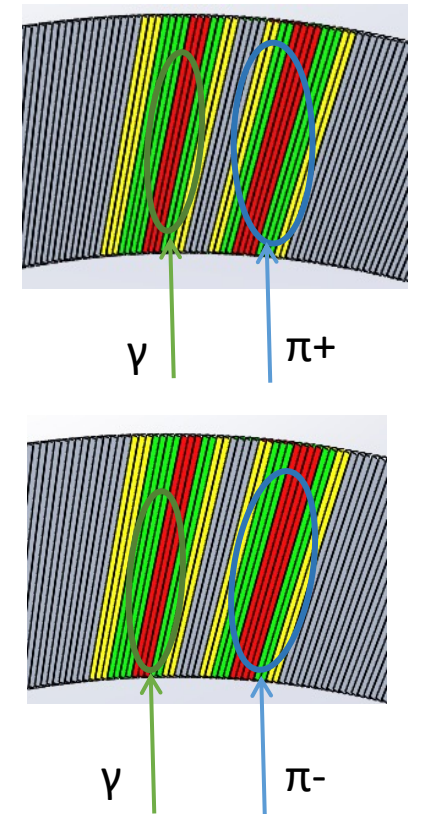


# Separation between $\gamma/\pi$

- 5 GeV  $\gamma$ /10GeV  $\pi$ , vary distance along  $\phi$  between them
- Separation use end-to-end NN
- Success reconstruction:  $3.3\text{GeV} < E_\gamma < 6.6\text{GeV}$  not yet applied
- Different  $\pi/\gamma$  separation power: pointing angle / magnetic field



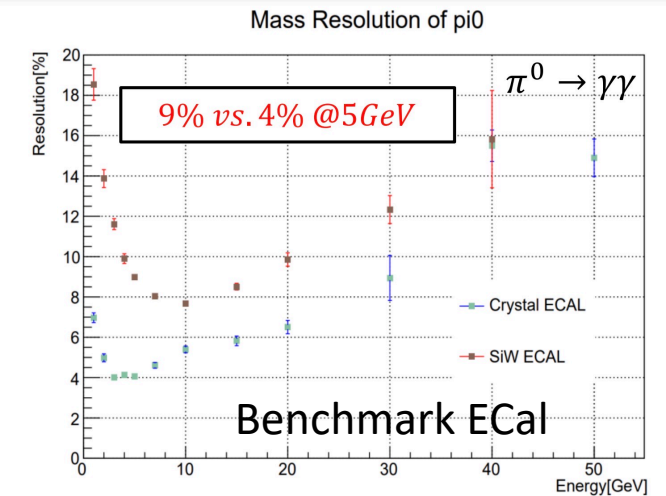
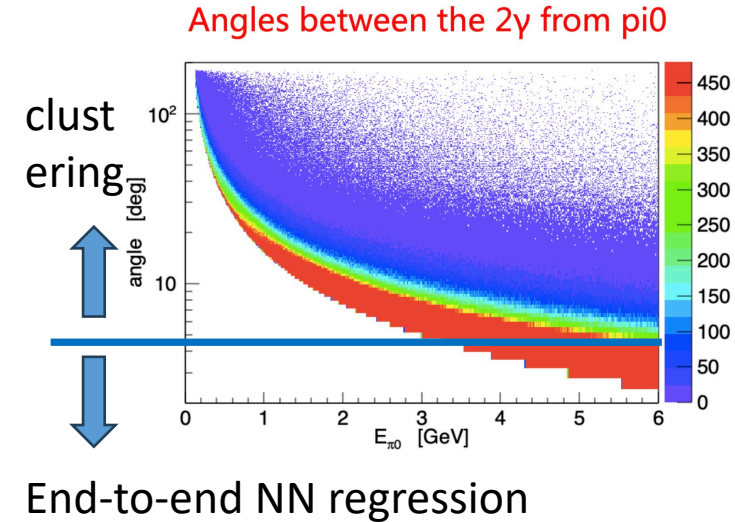
<https://journals.aps.org/prd/pdf/10.1103/PhysRevD.108.052002>



Trained with a sample of 1-10GeV  $\gamma$ , 2-20GeV  $\pi^+$ , distance @calor varied around 20 mm

# Pi0 → 2photon invariant mass

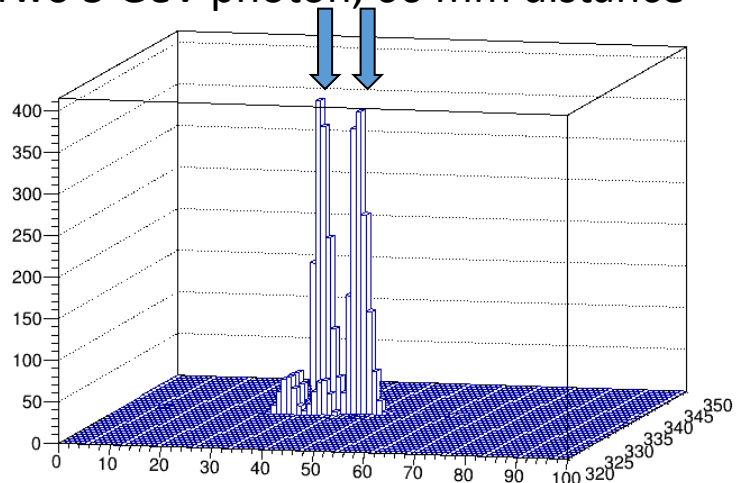
- End-to-end NN regression is used
  - Trained with di-photon events with flat distributed momentum from x GeV to XX GeV, distant < 3 degree
  - Apply to samples of pi0 → di-photon with different pi0 moment



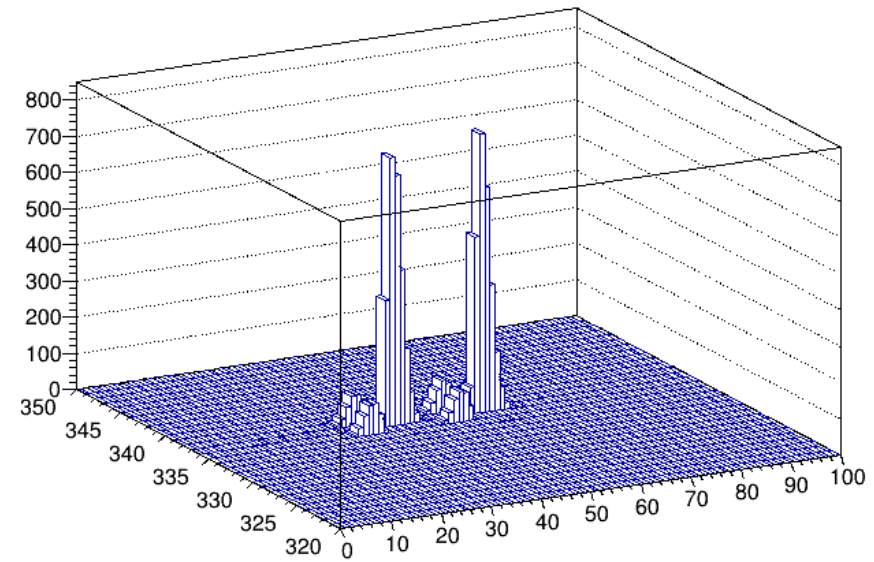
$$\frac{\delta m_0}{m_0} = \frac{\delta E_1}{2E_1} \oplus \frac{\delta E_2}{2E_2} \oplus \cot \frac{\alpha}{2} \frac{\delta \alpha}{2}$$

# Event display of shower separation/ID

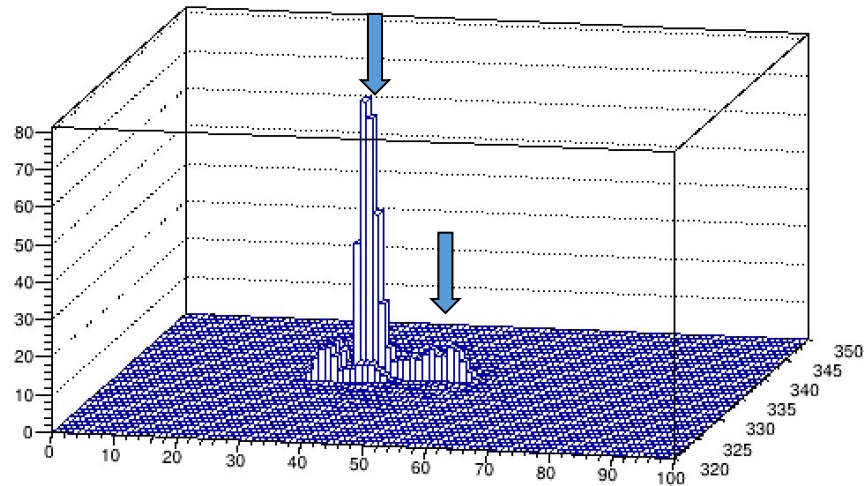
Two 5 GeV photon, 66 mm distance



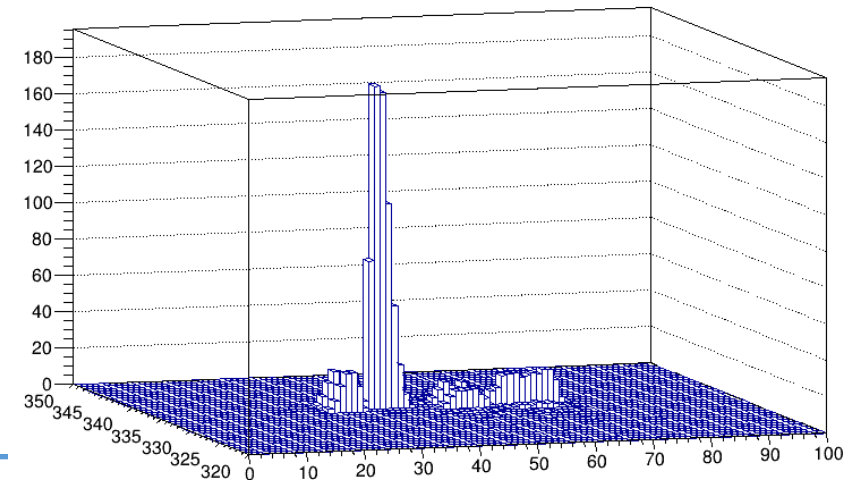
Two 5 GeV photon, 165 mm distance



5 GeV photon and 10 GeV pi-, 66mm




5 GeV photon and 10 GeV pi-, 195mm





# SiPM vs APD

- SiPM
  - 60 RMB/piece (From HGCal)
    - 3\*3 mm
  - $10^{10} n_{eq}/cm^2$  ( $10^{14} n_{eq}/cm$ )
    - R&D at IHEP
- APD
  - 20 RMB/piece (From 高能瑞泰, 仿制滨松)
    - 3\*3 mm
    - R&D needed?
  - Used on CMS (S8664-55)

Package type	 face mount type
Number of channels	1 ch
Effective photosensitive area / ch	3 × 3 mm
Number of pixels /ch	89984m
Pixel size	10 μm
Spectral response range	290 to 900 nm
Peak sensitivity wavelength (typ.)	460 nm
Dark count/ch (typ.)	700 kcps
Terminal capacitance/ch (typ.)	530 pF
Gain (typ.)	$1.8 \times 10^5$
Measurement condition	Ta=25 °C

**S14160-3010PS**

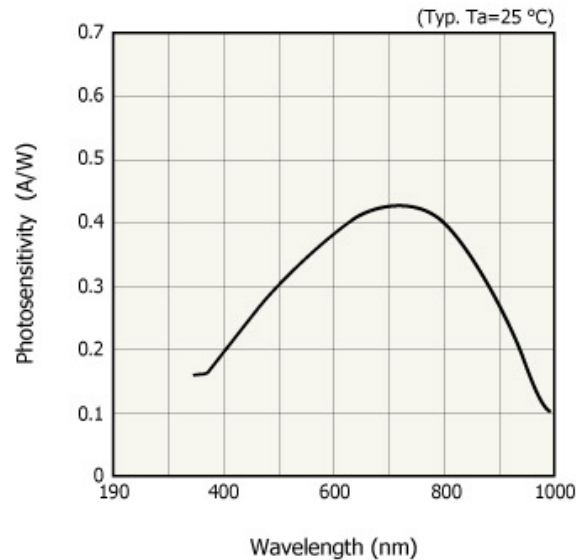
Peak sensitivity wavelength (typ.)	600 nm
Spectral response range	320 to 1000 nm
Photosensitivity (typ.)	0.24 A/W
Dark current (max.)	50 nA
Cutoff frequency (typ.)	40 MHz
Terminal capacitance (typ.)	80 pF
Breakdown voltage (typ.)	400 V
Temperature coefficient of BV	0.78 V/°C
Gain (typ.)	50
Measurement condition	Typ. Ta=25 °C, unless otherwise noted,
	Photosensitivity: λ=420 nm, M=1

**S8664-55**

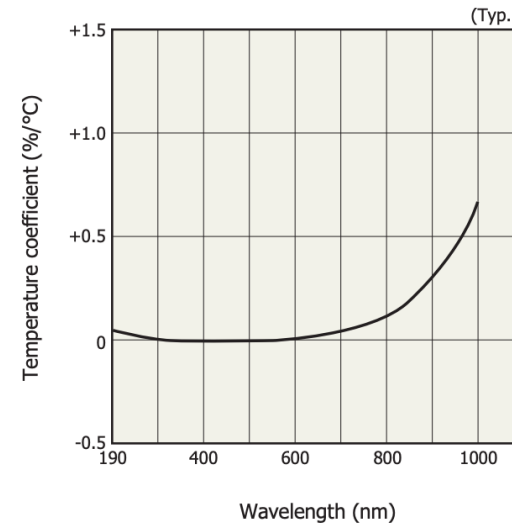
# PD

34	Photosensitive area	2.4 × 2.4 mm
35	Number of elements	1c
36	Package	Ceramic
37	Cooling	Non-cooled
38	Reverse voltage (max.)	5 V
39	Spectral response range	340 to 1000 nm
40	Peak sensitivity wavelength (typ.)	720 nm
41	Photosensitivity (typ.)	0.43 A/W
42	Dark current (max.)	5 pA
43	Rise time (typ.)	0.5 μs
44	Terminal capacitance (typ.)	160 pF
45	Noise equivalent power (typ.)	$2.1 \times 10^{-15}$ W/Hz <sup>1/2</sup>
46	Measurement condition	Typ. Ta=25 °C, Photosensitivity: λ=720 nm, Dark

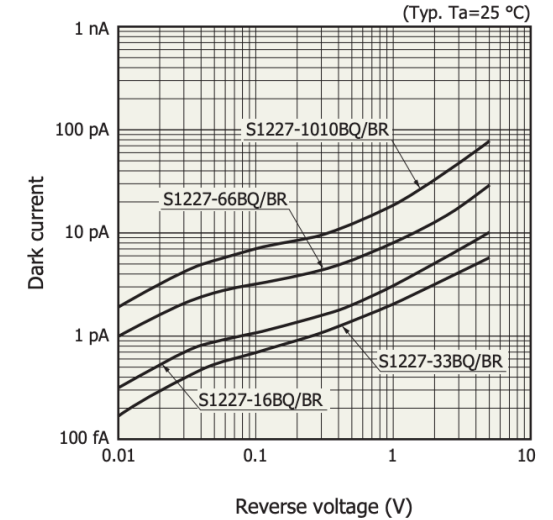
## S1227-33BR



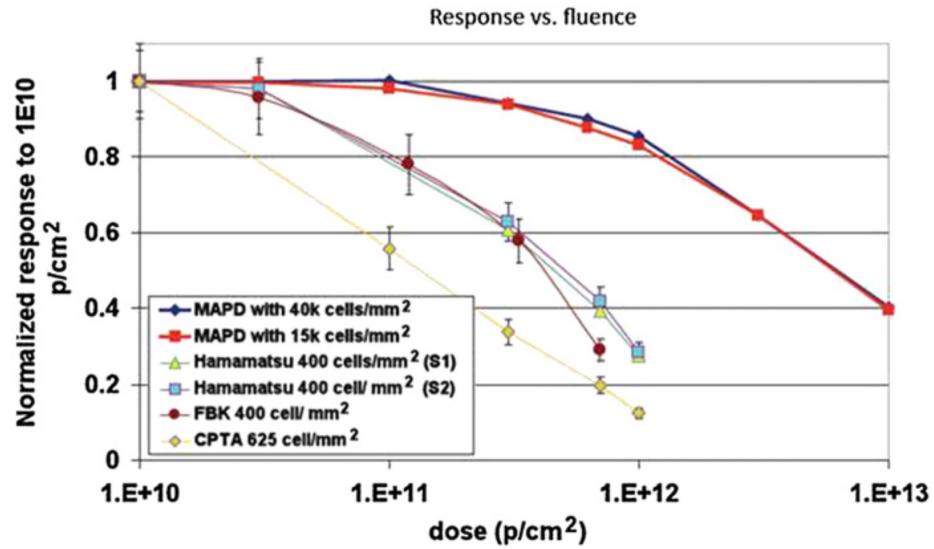
Photosensitivity temperature characteristics



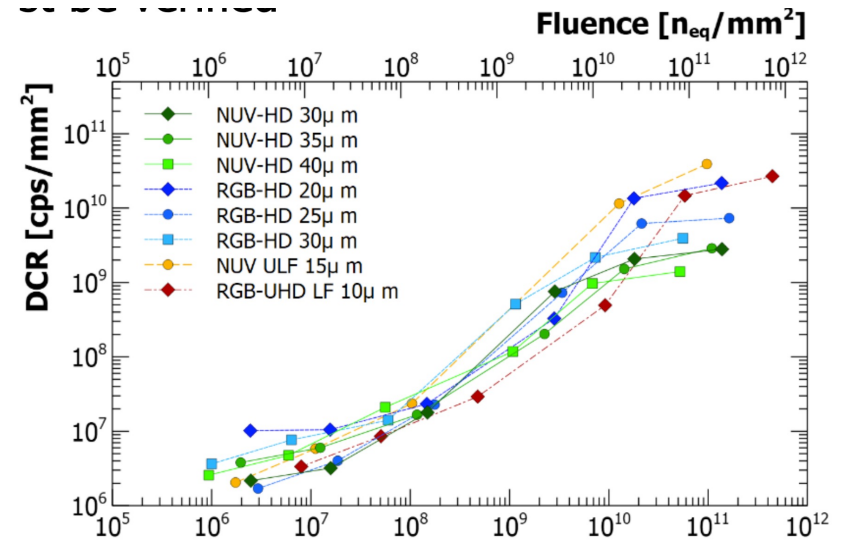
Dark current vs. reverse voltage



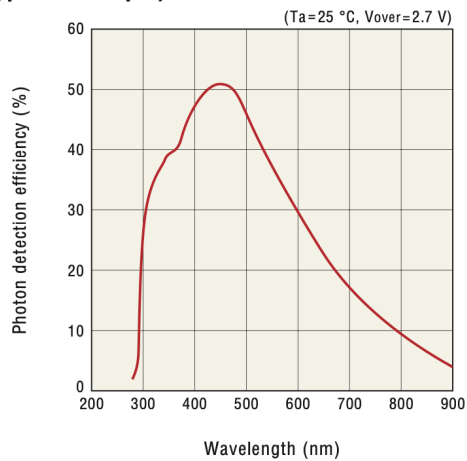
## SiPM的信号幅度 VS 辐照剂量



## SiPM的暗计数 VS 辐照剂量

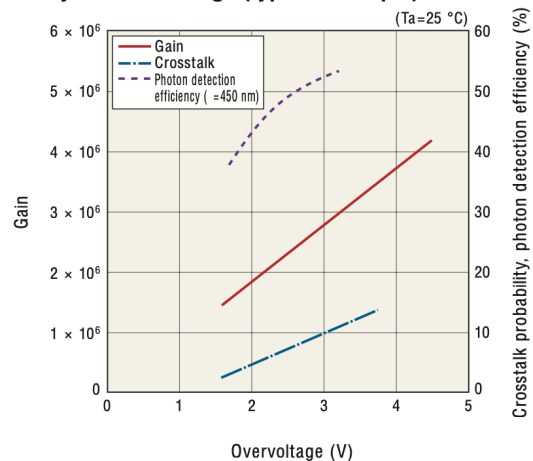


### Photon detection efficiency vs. wavelength (typical example)



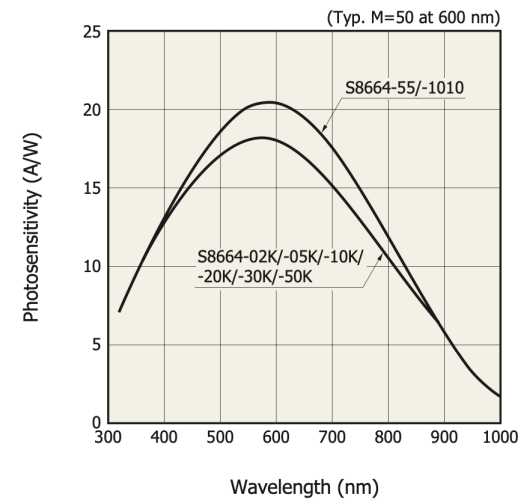
KAPD0599EB

### Gain, crosstalk probability, photon detection efficiency vs. overvoltage (typical example)



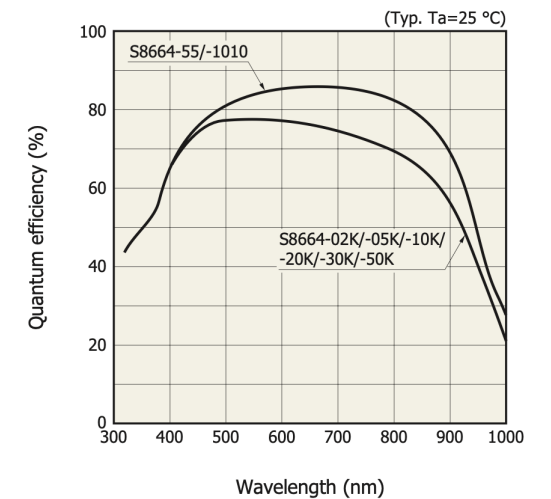
KAPD0582EA

### Spectral response



KAPD0073ED

### Quantum efficiency vs. wavelength



KAPD0074ED

# SiPM vs APD vs PD

	SiPM (S14160-3010PS)	APD (S8664-55)	PD (S1227-33BR)
价格	中 (较高)	中 (有不确定性)	低
单光子测量	是	否	否
时间测量	~10ps (lab)	~1ns (CMS)	?
线性范围	差	好	好
抗辐照	中	强	中
是否满足Stereo Ecal要求	是	是	是
刻度...	单光子	激光	氙气灯
已有实验		CMS	L3(its PD is not available now)

BGO: 8-10 photon/keV

Lower threshold: 2MeV: → 20,000 photons \* efficiency

### Active Elements:

- Hexagonal modules based on Si sensors in CE-E and high-radiation regions of CE-H
- “Cassettes”: multiple modules mounted on cooling plates with electronics and absorbers
- Scintillating tiles with on-tile SiPM readout in low-radiation regions of CE-H

### Key Parameters:

Coverage:  $1.5 < |\eta| < 3.0$

~215 tonnes per endcap

Full system maintained at  $-30^{\circ}\text{C}$

~620m<sup>2</sup> Si sensors in ~26000 modules

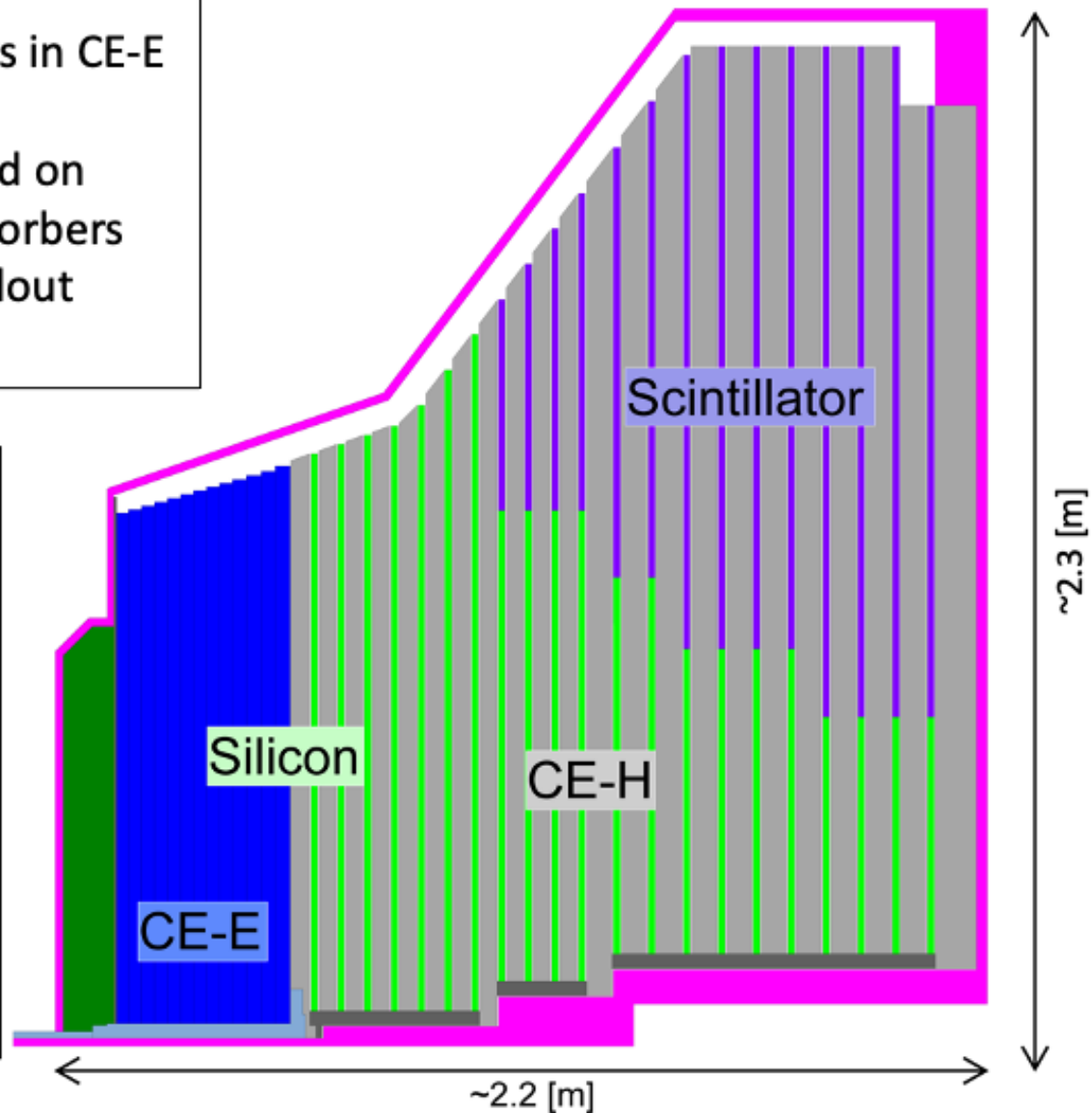
~6M Si channels, 0.6 or 1.2cm<sup>2</sup> cell size

~370m<sup>2</sup> of scintillators in ~3700 boards

~240k scint. channels, 4-30cm<sup>2</sup> cell size

Power at end of HL-LHC:

~125 kW per endcap



Electromagnetic calorimeter (CE-E): **Si**, Cu & CuW & Pb absorbers, 26 layers,  $27.7 X_0$  &  $\sim 1.5\lambda$   
Hadronic calorimeter (CE-H): **Si** & **scintillator**, steel absorbers, 21 layers,  $\sim 8.5\lambda$

# Cost from CMS HGCal (kCHF)

- Electronics: 6M Si + 240k Sc

4.6.1	Front-end System (Silicon sensors)	5,778
4.6.2	Front-end System (Scintillator/SiPM sensors)	872
4.6.3	Front-end System (Common to Silicon and SiPM)	4,164
4.6.4	Clock and Control	500
4.6.5	Power Distribution	4,448
<b>4.6</b>	<b>Electronics and Electrical Systems</b>	<b>15,762</b>
4.7.1	DAQ	2,447
4.7.2	Trigger	3,779
<b>4.7</b>	<b>Backend System (Trigger and DAQ)</b>	<b>6,226</b>
4.8.1	DCS	257
4.8.2	DSS	341
<b>4.8</b>	<b>Slow control</b>	<b>598</b>

SiPM + Sc. (4-30 cm<sup>2</sup> cell, 240k ch, 370 m<sup>2</sup>, X mm thick)

4.5.1	SiPM - Photosensors	1,718
4.5.2	Plastic scintillator	832
4.5.3	Wrapping (ESR film)	111
4.5.4	Assembly Centre and Tooling	270
4.5.5	Scintillator/SiPM Module Production	14
<b>4.5</b>	<b>Scintillator/SiPM Modules</b>	<b>2,945</b>

Si sensors: 620 m<sup>2</sup>

4.3	Silicon Sensors	21,513
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item	Power	SiPM	Plasic Sc. Mat.	FE	BE+Slow C.	Si
numbers	40 mW/ch	7.2CHF/ch	0.22CHF/cm <sup>2</sup>	2.5CHF/ch	1.1CHF/ch	3.5CHF/cm <sup>2</sup>
remarks	Half? in e+e	3*3 mm <sup>2</sup>	No wrapping			

# L3 BGO calorimeter:

$$\sigma(E)/E = 3.2\%/\sqrt{E} \oplus 0.9\%$$

## L3: BGO+PD:

- 1200 electron (0.2fC) per MeV shower energy
- Dynamical range: 1MeV to 200 GeV

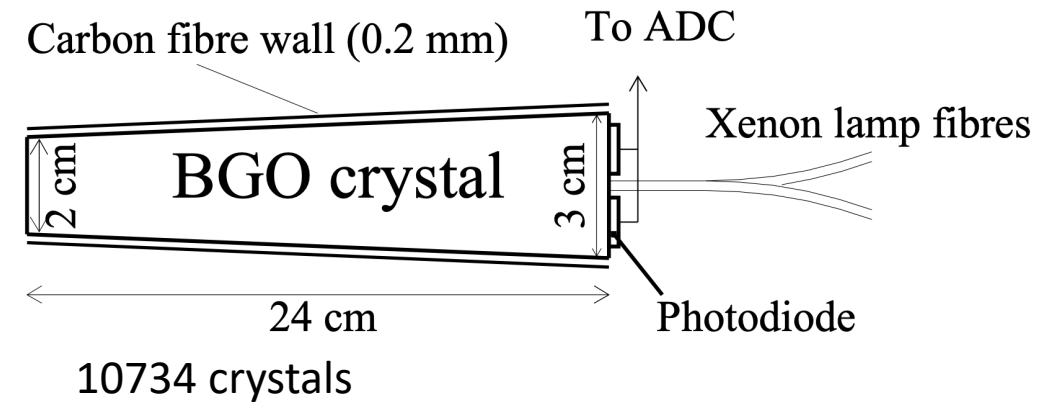


Figure 4.10: A BGO crystal.

decreased strongly (up to 50%) with the distance from the front face. After coating the crystals with a 40-50  $\mu\text{m}$  thick layer of high reflectivity white paint, the maximum variations in the collected light flux as a function of the distance from the front face were only about 5%.<sup>10</sup>

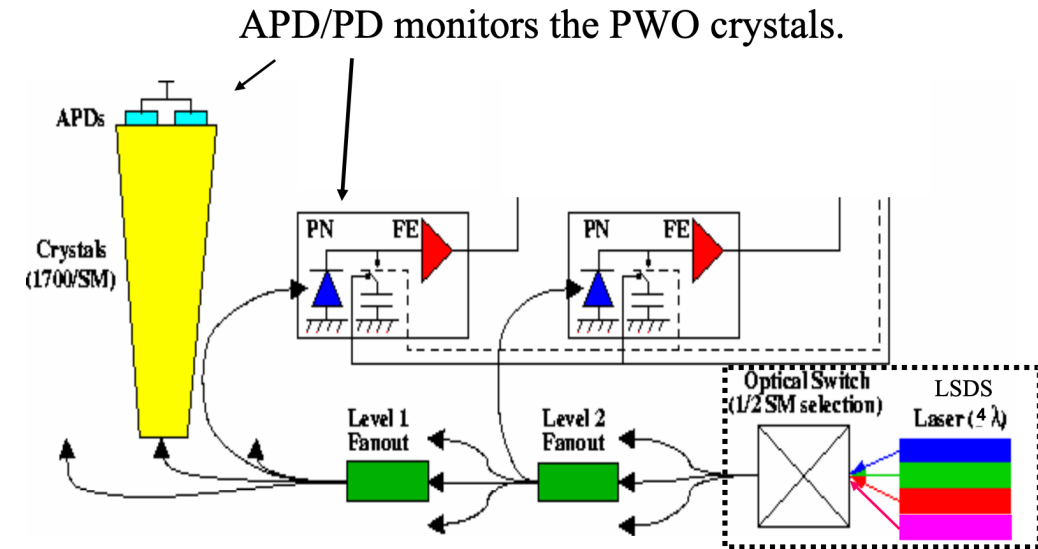
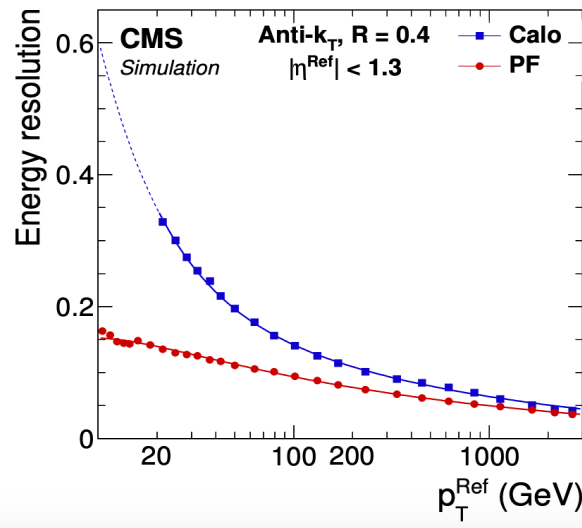
<sup>10</sup>The variations in the crystal light yield were measured using cosmic muons and were required to be less than 10% for all accepted BGO crystals [109].

shape (Figure 4.10) with a front surface of  $\simeq 2 \times 2 \text{ cm}^2$ , a rear surface of  $\simeq 3 \times 3 \text{ cm}^2$ , and a depth of about 21.5 radiation lengths (24 cm). To minimize the mechanical stress, each crystal was housed in its own cell of a carbon fiber support structure. The walls between the crystals were about 0.2 mm thick. The dead material of the walls together with the clearances represented about 2.1% of the solid angle coverage of the ECAL.

# CMS PWO calorimeter

- CMS: PWO+APD
  - 30MeV-2TeV

Contribution	Barrel ( $\eta = 0$ )	Endcap ( $\eta = 2$ )
Total stochastic term	2.7%/√E	5.7%/√E
Total constant term	0.55%	0.55%
Total noise (low luminosity) in $E_T$	155 MeV	205 MeV
Total noise (high luminosity) in $E_T$	210 MeV	245 MeV



The ECAL light monitoring system consists of laser source, optical switch based high-level distribution system and two level fanout system.